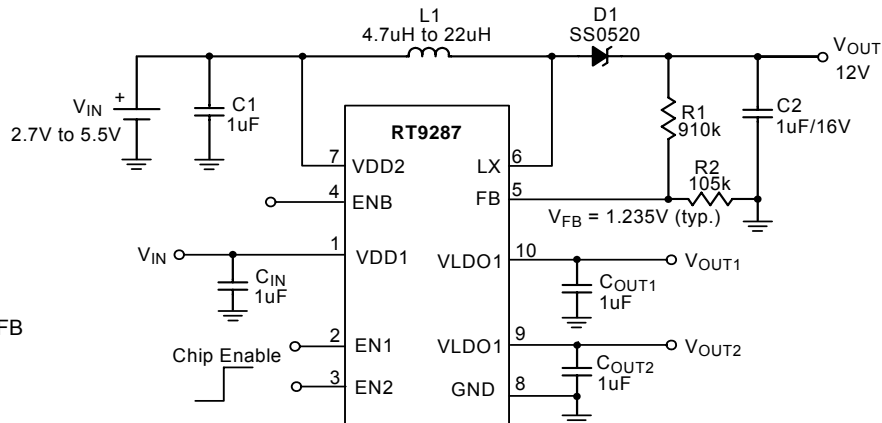




Typical Application Circuit



$$V_{OUT} = \frac{R1+R2}{R2} \times V_{FB}$$

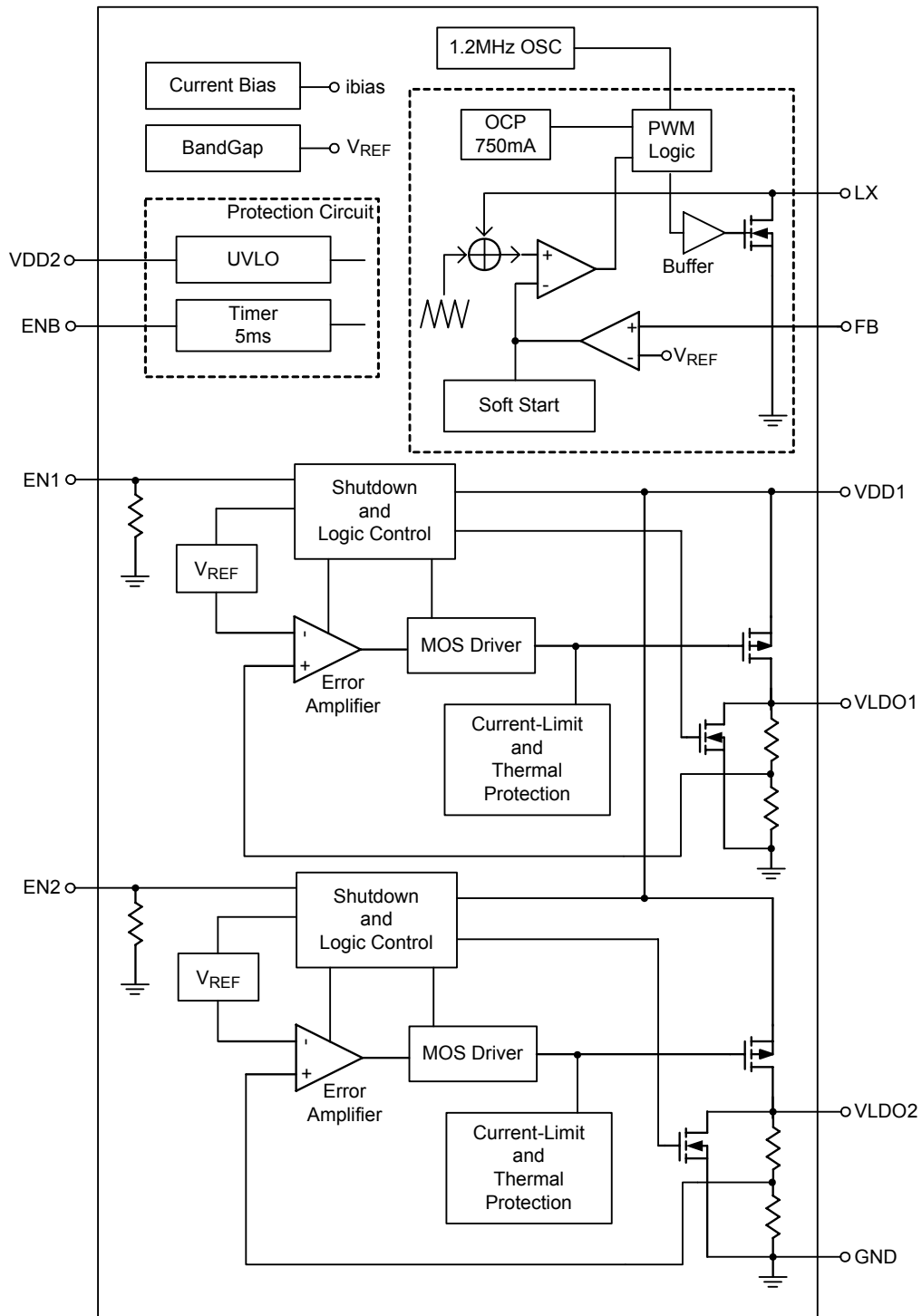
$$V_{FB} = 1.235 \text{ (typ.)}$$

$$R2 > 100k\Omega$$

Functional Pin Description

Pin No.	Pin Name	Pin Function
1	VDD1	LDO Power Input Voltage.
2	EN1	LDO Channel 1 Enable. (Active High).
3	EN2	LDO Channel 2 Enable. (Active High).
4	ENB	Boost Enable (Active High). Voltage sensing input to trigger the function of over voltage protection. Note that this pin is high impedance. There should be a pull low 100kΩ resistor connected to GND when the control signal is floating.
5	FB	Boost Feedback Reference Voltage Pin. Series connect a resistor between WLED and ground as a current sense. Sense the current feedback voltage to set the current rating.
6	LX	Boost Switch Pin. Connect this Pin to inductor and catch diode. Minimize the track area to reduce EMI.
7	VDD2	Boost Supply Input Voltage Pin. Bypass 1μF capacitor to GND to reduce the input noise.
8	GND	GND pin should be soldered to PCB board and connected to GND.
9	VLDO2	LDO Channel 2 Output Voltage.
10	VLDO1	LDO Channel 1 Output Voltage.
Exposed Pad (11)	GND	The exposed pad must be soldered to a large PCB and connected to GND for maximum power dissipation.

**Function Block Diagram**



**Absolute Maximum Ratings** (Note 1)

- Supply Input Voltage,  $V_{DD}$  ----- -0.3V to 7V
- LX Input Voltage ----- -0.3V to 22V
- The Other Pins ----- -0.3V to 6V
- Power Dissipation,  $P_D$  @  $T_A = 25^\circ\text{C}$   
 WDFN-10L 3x3 ----- 0.926W
- Package Thermal Resistance (Note 4)  
 WDFN-10L 3x3,  $\theta_{JA}$  ----- 108°C/W  
 WDFN-10L 3x3,  $\theta_{JC}$  ----- 8.2°C/W
- Junction Temperature ----- 150°C
- Lead Temperature (Soldering, 10 sec.) ----- 260°C
- Storage Temperature Range ----- -65°C to 150°C
- ESD Susceptibility (Note 2)  
 HBM (Human Body Mode) ----- 2kV  
 MM (Machine Mode) ----- 200V

**Recommended Operating Conditions** (Note 3)

- Supply Input Voltage Range ----- 2.7V to 5.5V
- Junction Temperature Range ----- -40°C to 125°C
- Ambient Temperature Range ----- -40°C to 85°C

**Electrical Characteristics**

( $V_{DD2} = 3.7\text{V}$ ,  $V_{DD1} = V_{OUT} + 1\text{V}$ ,  $V_{EN} = V_{IN}$ ,  $C_{IN} = C_{OUT} = 1\mu\text{A}$ ,  $T_A = 25^\circ\text{C}$ , unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
<b>Boost</b>						
<b>System Supply Input</b>						
Operating Voltage Range	$V_{DD2}$		2.7	--	5.5	V
Under Voltage Lockout	$V_{DD2}$		--	2.2	--	V
Quiescent Current	$I_{DD2}$	$V_{FB} = 1.5\text{V}$ , No switch	--	300	--	$\mu\text{A}$
Supply Current	$I_{DD2}$	$V_{FB} = 0\text{V}$ , Switch	--	2	--	mA
Shut Down Current	$I_{DD2}$	$V_{ENB} < 0.4\text{V}$	--	--	1	$\mu\text{A}$
Line Regulation		$V_{DD2} = 3.0\text{V}$ to $4.3\text{V}$	--	3	--	%
<b>Oscillator</b>						
Operating Frequency	$f_{OSC}$		--	1.2	--	MHz
Maximum Duty Cycle			85	--	--	%
<b>Reference Voltage</b>						
Feedback Reference Voltage	$V_{REF}$		1.173	1.235	1.296	V
<b>MOSFET</b>						
On Resistance of MOSFET	$R_{DS(ON)}$		--	0.75	--	$\Omega$
OCP			--	750	--	mA
Enable Voltage Low	$V_{EN\_L}$		--	--	0.4	V
Enable Voltage High	$V_{EN\_H}$		1.5	--	--	V

To be continued

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
<b>Dual LDO</b>						
Input Voltage	V <sub>DD1</sub>	V <sub>DD</sub> = 2.7V to 5.5V	2.7	--	5.5	V
Dropout Voltage (Note 5)	V <sub>DROP</sub>	I <sub>OUT</sub> = 150mA	--	120	--	mV
		I <sub>OUT</sub> = 300mA	--	240	--	mV
Output Voltage Range	V <sub>LDO1</sub> , V <sub>LDO2</sub>		1.2	--	3.6	V
V <sub>LDO1,2</sub> Accuracy	ΔV	I <sub>OUT</sub> = 1mA	-2	--	+2	%
Line Regulation	ΔV <sub>LINE</sub>	V <sub>DD1</sub> = (V <sub>LDO1,2</sub> + 0.3V) to 5.5V or V <sub>DD1</sub> > 2.7V, whichever is larger	--	--	0.2	%
Load Regulation	ΔV <sub>LOAD</sub>	1mA < I <sub>OUT</sub> < 300mA	--	--	0.6	%
Current Limit		R <sub>LOAD</sub> = 1Ω	330	450	700	mA
Quiescent Current	I <sub>Q</sub>	V <sub>EN1,2</sub> > 1.5V	--	58	80	μA
Shutdown Current	I <sub>SHDN</sub>	V <sub>EN1,2</sub> < 0.4V	--	--	1	μA
EN1,2 Threshold	V <sub>IH</sub>	V <sub>DD</sub> = 2.7V to 5.5V, Power On	1.5	--	--	V
	V <sub>IL</sub>	V <sub>DD</sub> = 2.7V to 5.5V, Shutdown	--	--	0.4	V
Output Voltage TC			--	100	--	ppm/°C
Thermal Shutdown	T <sub>SD</sub>		--	165	--	°C
Thermal Shutdown Hysteresis	ΔT <sub>SD</sub>		--	40	--	°C
Thermal Shutdown Hysteresis	ΔT <sub>SD</sub>		--	40	--	°C
PSRR I <sub>LOAD</sub> = 10mA	PSRR	f = 100Hz	--	65	--	dB
		f = 1kHz	--	60	--	dB
		f = 10kHz	--	50	--	dB
PSRR I <sub>LOAD</sub> = 150mA		f = 100Hz	--	65	--	dB
		f = 1kHz	--	50	--	dB
		f = 10kHz	--	50	--	dB

**Note 1.** Stresses listed as the above "Absolute Maximum Ratings" may cause permanent damage to the device. These are for stress ratings. Functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may remain possibility to affect device reliability.

**Note 2.** Devices are ESD sensitive. Handling precaution recommended.

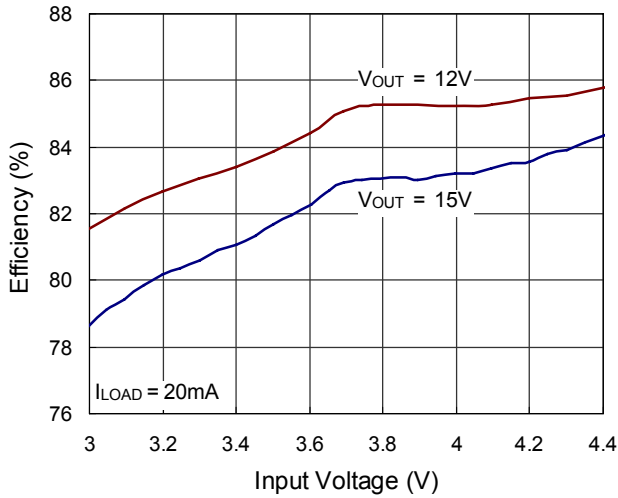
**Note 3.** The device is not guaranteed to function outside its operating conditions.

**Note 4.** θ<sub>JA</sub> is measured in the natural convection at T<sub>A</sub> = 25°C on a low effective thermal conductivity test board of JEDEC 51-3 thermal measurement standard. The case point of θ<sub>JC</sub> is on the expose pad for the WDFN package.

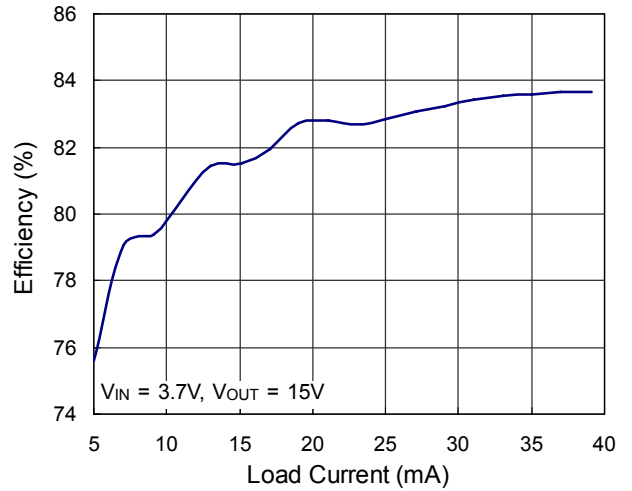
**Note 5.** The dropout voltage is defined as V<sub>IN</sub> - V<sub>OUT</sub>, which is measured when V<sub>OUT</sub> is V<sub>OUT(NORMAL)</sub> - 100mV.

Typical Operating Characteristics

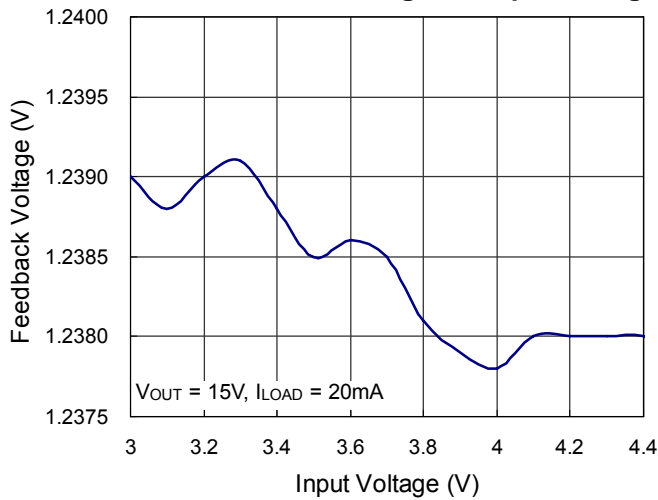
Boost Efficiency vs. Input Voltage



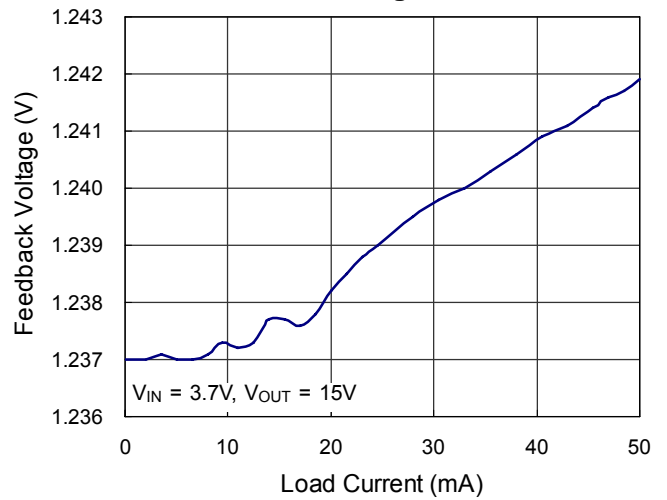
Boost Efficiency vs. Load Current



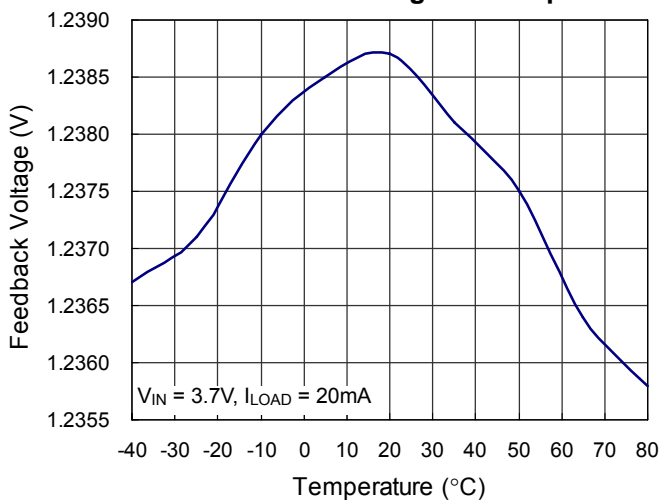
Boost Feedback Voltage vs. Input Voltage



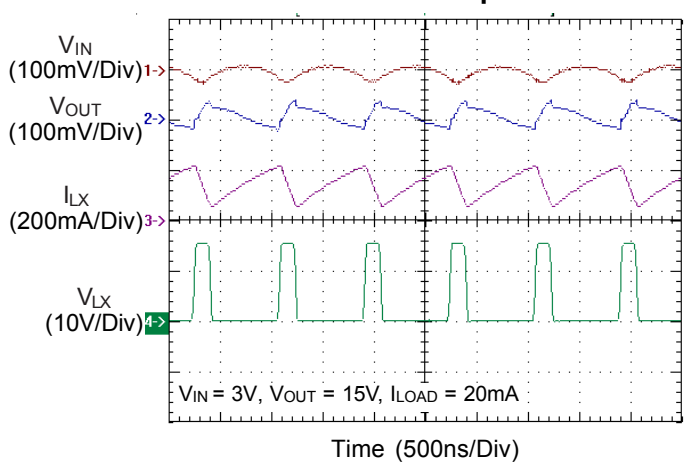
Boost Feedback Voltage vs. Load Current



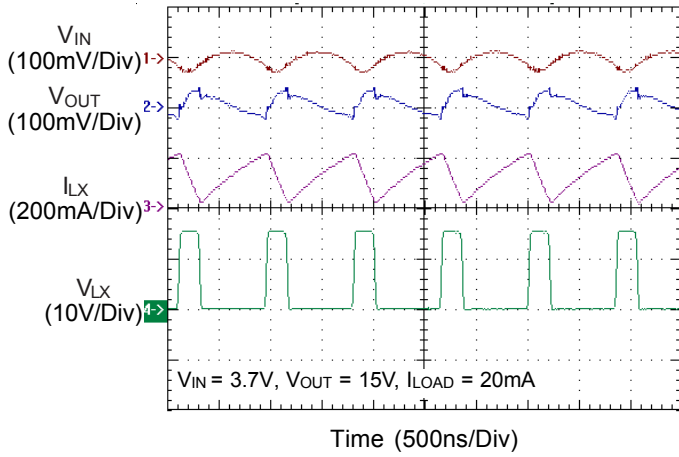
Boost Feedback Voltage vs. Temperature



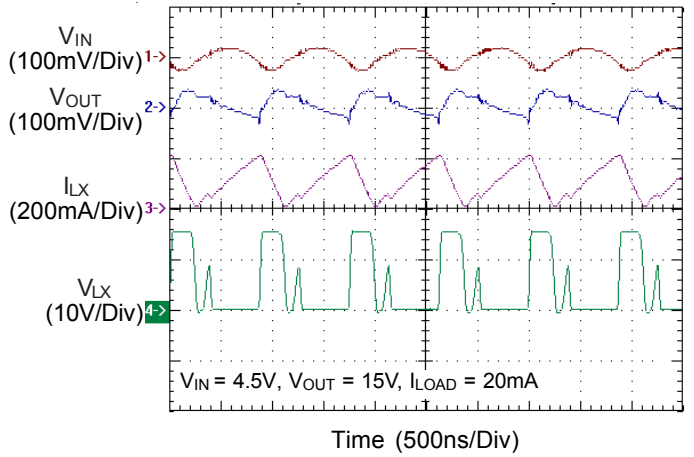
Boost Normal Operation



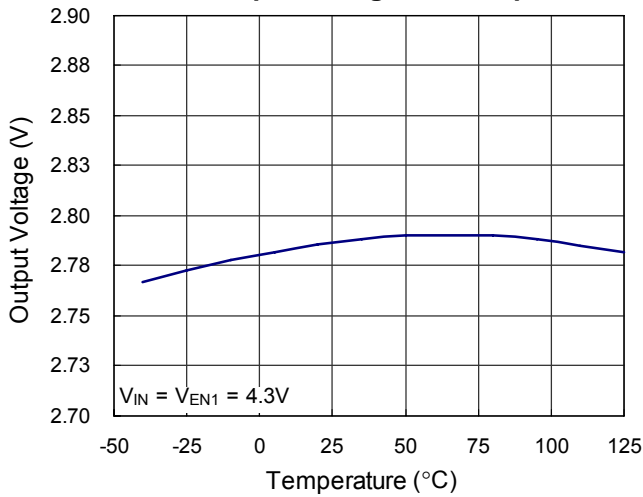
Boost Normal Operation



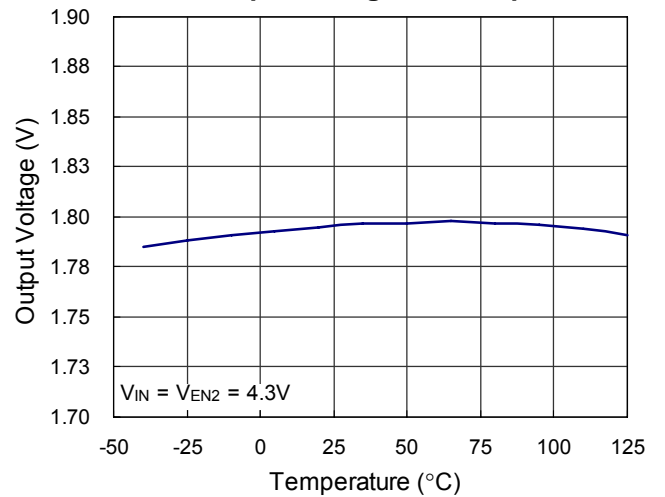
Boost Normal Operation



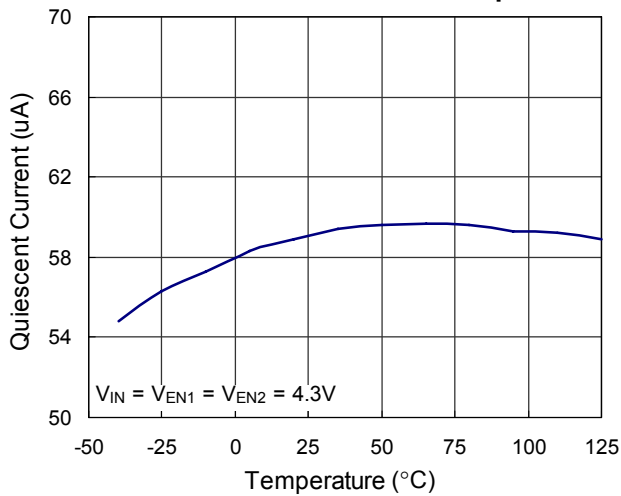
LDO 1 Output Voltage vs. Temperature



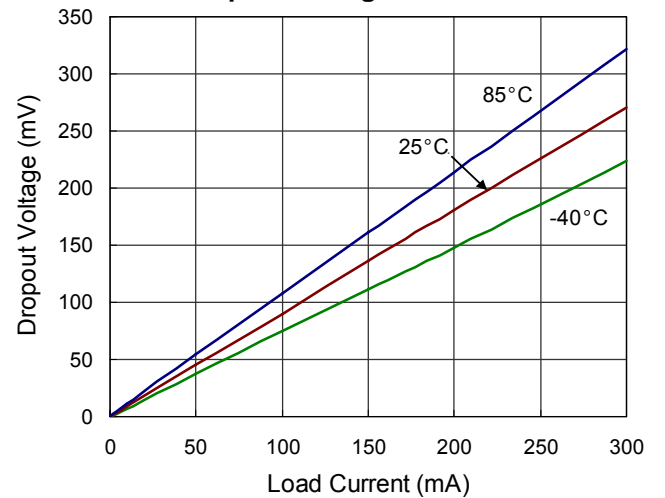
LDO 2 Output Voltage vs. Temperature

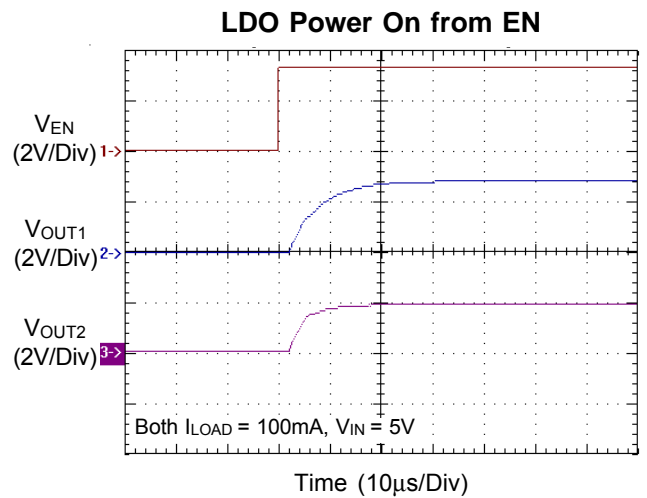
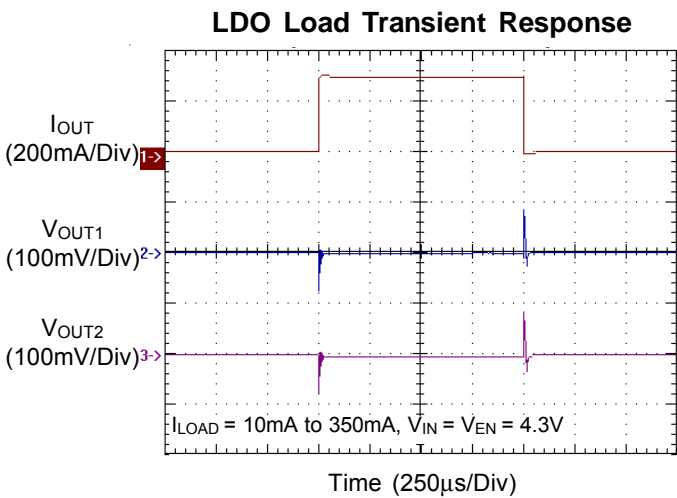
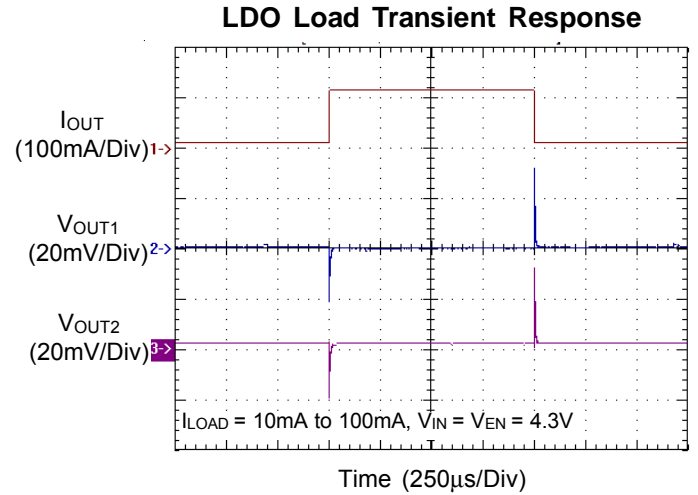
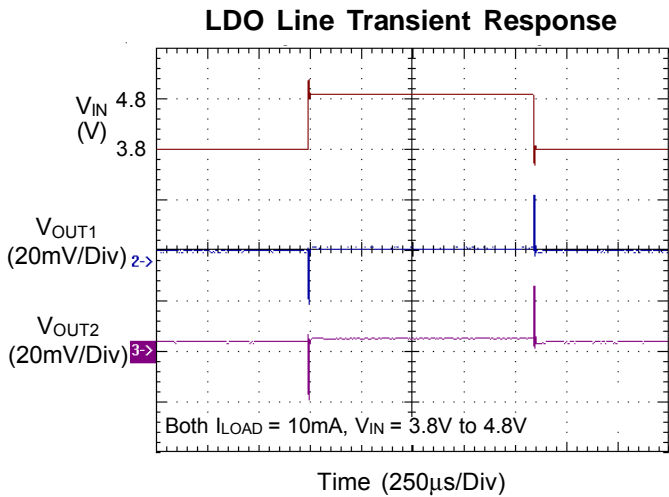
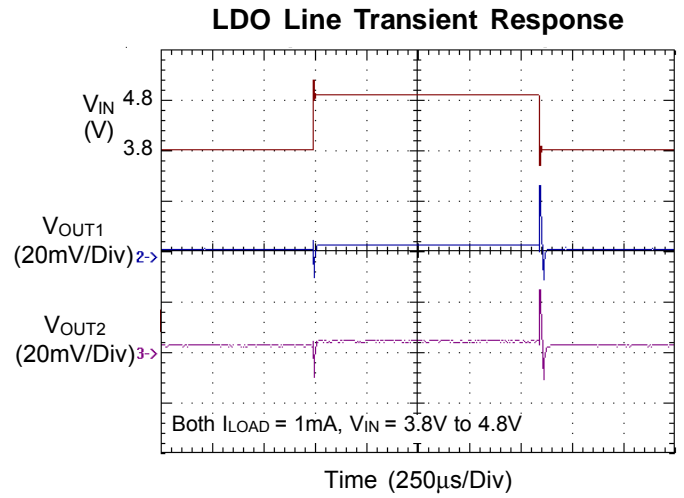
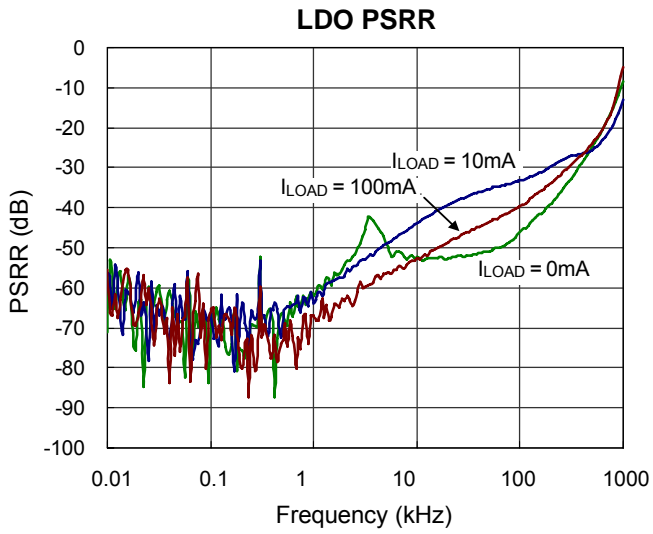


LDO Quiescent Current vs. Temperature



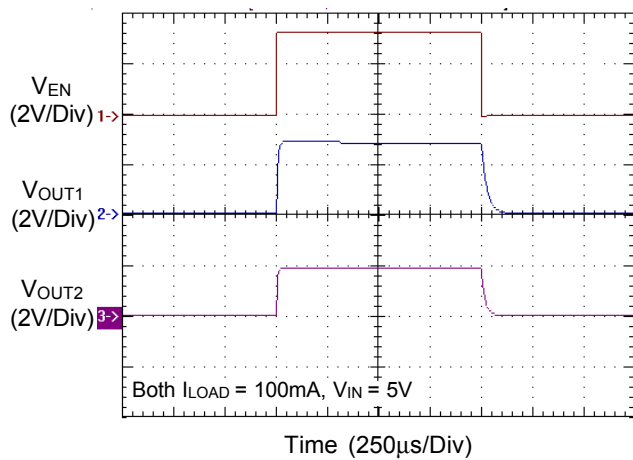
LDO Dropout Voltage vs. Load Current



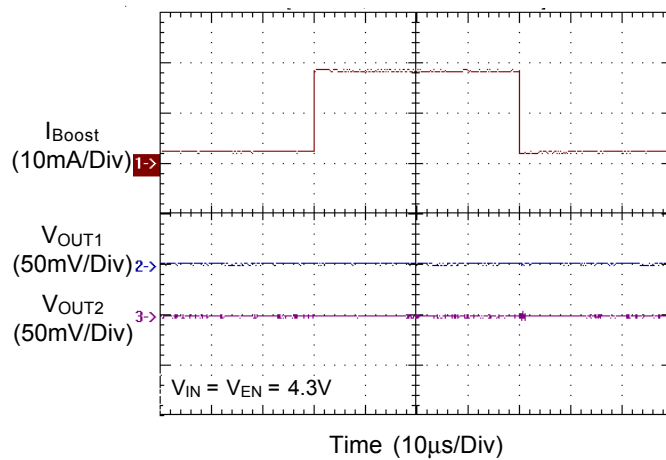




LDO Power Off from EN



Cross Talk



## Application Information

### Boost Converter

#### Power Sequence

The RT9287 must take notice of the power sequence. The power sequence of RT9287 has to VDD2 early than ENB or else the RT9287 maybe fall into the unknown state to result in RT9287 turn off.

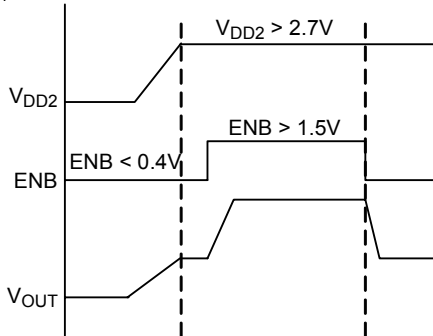


Figure 1

#### LED Current Control

As shown in Figure 2, the RT9287 regulates the LED current by setting the current sense resistor ( $R_{SET}$ ) connected between FB pin and ground. The reference voltage of FB pin is 1.235V in typical. The LED current ( $I_{LED}$ ) can be calculated by the following Equation.

$$I_{LED} = V_{REF} / R_{SET} \tag{1}$$

In order to have an accurate LED current, a precision resistor is preferred (1% is recommended).

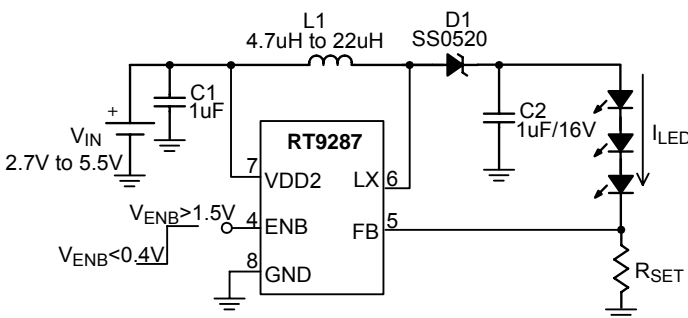


Figure 2. Application for Driving 3 Series WLEDs

#### Inductor Selection

The recommended value of the inductor is from 10μH to 22μH for 4 to 5 WLEDs applications. For 3WLEDs, the recommended value of the inductor is from 4.7μH to 22μH. Small size and better efficiency are the major concerns for portable devices, just as RT9287's application for mobile

phone. The inductor should have low core loss at 1MHz and low DCR for better efficiency.

The inductor saturation current rating should be considered to cover the inductor peak current.

#### Capacitor Selection

Input and output ceramic capacitors of 1μF are recommended for boost regulator. For better voltage filtering, ceramic capacitors with low ESR are recommended. X5R and X7R types are suitable because they have better temperature characteristics.

#### Diode Selection

Schottky diode is suitable for RT9287 because of its low forward voltage and fast reverse recovery. Using Schottky diode can get better efficiency. The high speed rectification is also a good characteristic of Schottky diode for high switching frequency. Current rating of the diode must meet the root mean square of the peak current and output average current multiplication as following :

$$I_D(RMS) \approx \sqrt{I_{OUT} \times I_{PEAK}}$$

The reverse breakdown voltage of the diode should be higher than the output voltage.

#### Output Voltage Control

For fixed output voltage application, the output voltage can be adjusted by the divider circuit on FB pin. Figure 3 shows a 2-level voltage control circuit for OLED application. The output voltage can be calculated by the following equations. Table 1 is the recommended resistance for different conditions.

$$V_{OUT} = R_A \times \{ (F_B/R_B) + (F_B-GPIO)/R_{GPIO} \} + F_B \tag{3}$$

As GPIO = 0V,

$$V_{OUT} = R_A \times \{ (1.235/R_B) + (1.235/R_{GPIO}) \} + 1.235 \tag{4}$$

As GPIO = 2.8V,

$$V_{OUT} = R_A \times \{ (1.235/R_B) + (1.235-2.8)/R_{GPIO} \} + 1.235 \tag{5}$$

As GPIO = 1.8V,

$$V_{OUT} = R_A \times \{ (1.235/R_B) + (1.235-1.8)/R_{GPIO} \} + 1.235 \tag{6}$$

For Efficiency Consideration set  $R_A = 990k\Omega$ .

**Table 1. Suggested Resistance for Output Voltage Control**

Conditions	R <sub>A</sub> (kΩ)	R <sub>B</sub> (kΩ)	R <sub>GPIO</sub> (kΩ)
Case A: Normal Voltage = 16V (GPIO = 0V) Dimming Voltage = 12V (GPIO = 1.8V)	990	102	445
Case B: Normal Voltage = 16V (GPIO = 0V) Dimming Voltage = 12V (GPIO = 2.8V)	990	94	690

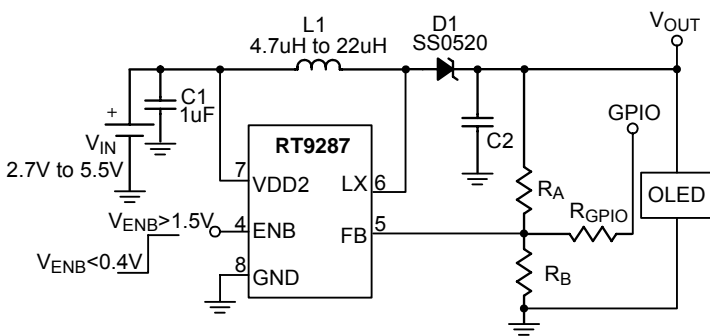


Figure 3. Application Circuit for 2-level Output Voltage Control

**Dual LDO**

Like any low-dropout regulator, the external capacitors used with the RT9287 must be carefully selected for regulator stability and performance. Using a capacitor whose value is > 1μF on the LDO input and the amount of capacitance can be increased without limit. The input capacitor must be located a distance of not more than 0.5 inch from the input pin of the IC and returned to a clean analog ground. Any high quality ceramic or tantalum capacitor can be used for this part. The capacitor with larger value and lower ESR (equivalent series resistance) provides better PSRR and line-transient response.

The output capacitor must meet both requirements for minimum amount of capacitance and ESR in all applications. The LDO is designed specifically to work with low ESR ceramic output capacitor in space-saving and performance consideration. Using a ceramic capacitor whose value is at least 1μF with ESR is > 20mΩ on the LDO output ensures stability. The LDO still works well with other kinds of output capacitor due to the wide stable ESR range. Figure 4 shows the curves of allowable ESR range as a function of load current for various output

capacitor values. Output capacitor of larger capacitance can reduce noise and improve load transient response, stability, and PSRR. The output capacitor should be located not more than 0.5 inch from the V<sub>OUT</sub> pin of the LDO and returned to a clean analog ground.

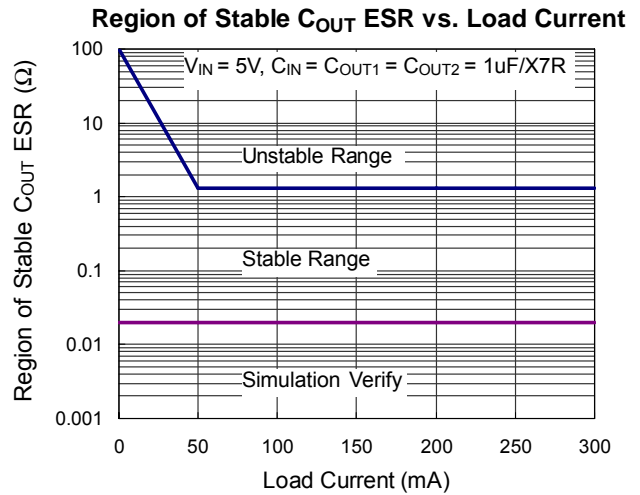


Figure 4. Stable C<sub>OUT</sub> ESR Range

Thermal protection limits power dissipation in LDO. When the operating junction temperature exceeds a certain temperature, the OTP circuit starts the thermal shutdown function and turns the pass element off. The pass element turns on again after the junction temperature is cooled down. The RT9287 lowers its OTP trip level from 170°C to 110°C when output short circuit occurs (V<sub>OUT</sub> < 0.4V) as shown in Figure 5. It reduces operating junction temperature and provides maximum safety to customer while output short circuit occurring.

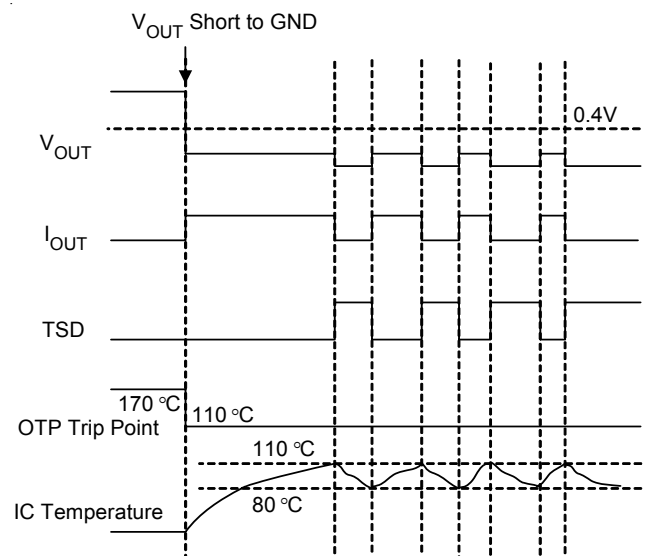


Figure 5. Short Circuit Thermal Folded Back Protection when Output Short Circuit Occurs (Patent)

**Thermal Considerations**

The maximum power dissipation depends on the thermal resistance of IC package, PCB layout, the rate of surroundings airflow and temperature difference between junctions to ambient. The maximum power dissipation can be calculated by following formula :

$$P_{D(MAX)} = (T_{J(MAX)} - T_A) / \theta_{JA}$$

Where  $T_{J(MAX)}$  is the maximum operation junction temperature,  $T_A$  is the ambient temperature and the  $\theta_{JA}$  is the junction to ambient thermal resistance.

For recommended operating conditions specification of the RT9287, where  $T_{J(MAX)}$  is the maximum junction temperature of the die and  $T_A$  is the maximum ambient temperature. The junction to ambient thermal resistance  $J_A$  is layout dependent. For WDFN-10L 3x3 packages, the thermal resistance  $J_A$  is 60°C/W on the standard JEDEC 51-7 four-layers thermal test board. The maximum power dissipation at  $T_A = 25^\circ\text{C}$  can be calculated by following formula :

$$P_{D(MAX)} = (125^\circ\text{C} - 25^\circ\text{C}) / (60^\circ\text{C/W}) = 1.667\text{W for WDFN-10L 3x3 packages}$$

The maximum power dissipation depends on operating ambient temperature for fixed  $T_{J(MAX)}$  and thermal resistance  $J_{J(MAX)}$ . For RT9287 packages, the Figure 6 of derating curves allows the designer to see the effect of rising ambient temperature on the maximum power allowed.

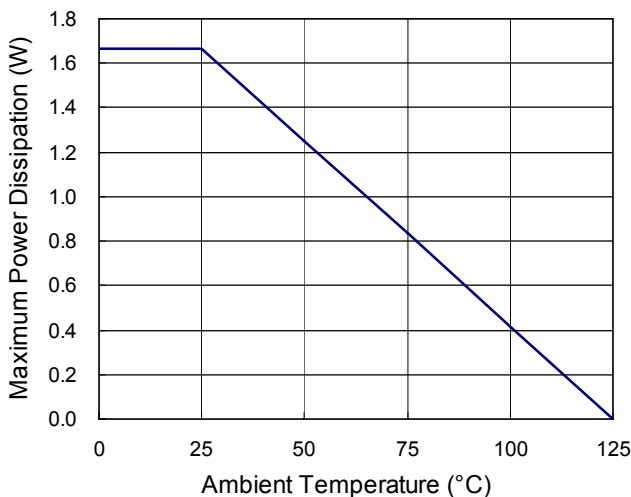


Figure 6. Derating Curves for RT9287 Packages

**Layout Guide**

The exposed pad and GND should be connected to a strong ground plane for heat sinking and noise prevention.

Traces should be kept as short as possible.

- ▶LX node copper area should be minimized for reducing EMI.
- ▶The Dual LDO input capacitor C1 must be located a distance of not more than 0.5 inch from the VDD1 pin and returned to ground plane.
- ▶The Boost input capacitor C2 should be placed as closed as possible to Pin 7.
- ▶The Dual LDO output capacitor C3 and C4 must be located a distance of not more than 0.5 inch from the VLDO1 and VLDO2 pin and returned to ground plane.
- ▶FB node copper area should be minimized and kept far away from noise sources (L<sub>x</sub>).
- ▶Feedback resistance R2 should be placed as closed as possible to Pin 5.

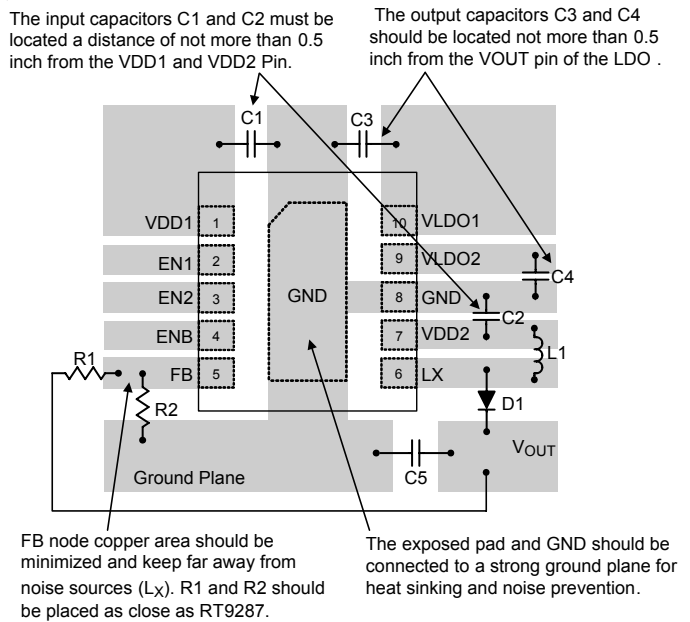
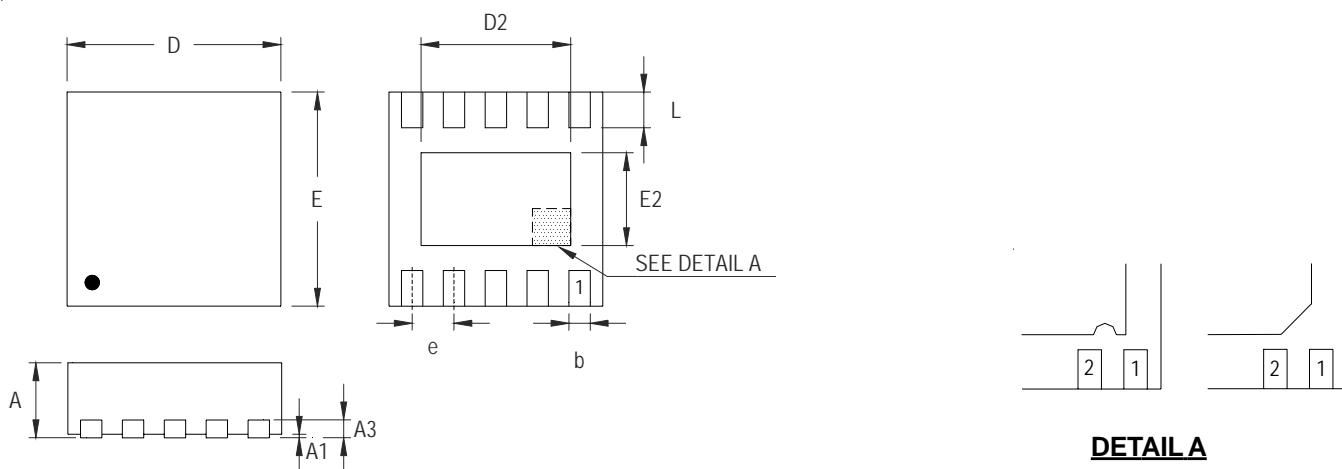


Figure 7

**Outline Dimension**



**DETAIL A**

Pin #1 ID and Tie Bar Mark Options

Note : The configuration of the Pin #1 identifier is optional, but must be located within the zone indicated.

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.700	0.800	0.028	0.031
A1	0.000	0.050	0.000	0.002
A3	0.175	0.250	0.007	0.010
b	0.180	0.300	0.007	0.012
D	2.950	3.050	0.116	0.120
D2	2.300	2.650	0.091	0.104
E	2.950	3.050	0.116	0.120
E2	1.500	1.750	0.059	0.069
e	0.500		0.020	
L	0.350	0.450	0.014	0.018

**W-Type 10L DFN 3x3 Package**

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